

CLAIMS

Nullcl > 21. (Amended) A conductive line comprising:
a polysilicon layer;
a metal-silicide layer against the layer of polysilicon, the metal-silicide layer
comprising a Group III dopant or a Group V dopant; and
a silicon-dioxide-containing dopant barrier layer against the metal-silicide
layer.

B1

22. The conductive line of claim 21 wherein the metal-silicide layer
comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.

23. Cancel.

24. Cancel.

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28. Cancel.

W&C 29. (New) The conductive line of claim 21 wherein the silicon-dioxide-containing dopant barrier layer is elevationally above the metal-silicide layer.

B2 30. (New) The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, and wherein the silicon-dioxide-containing dopant barrier layer is against the uppermost surface.

B2 31. (New) The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, the uppermost surface having a width dimension, and wherein the silicon-dioxide-containing dopant barrier layer is against substantially the entire width of the uppermost surface.